

TO-220F

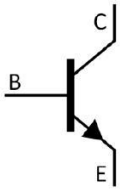
NPN

Silicon NPN transistor in a TO-220F Plastic Package.

2SB1375

Low $V_{CE(sat)}$, High total power dissipation, complementary pair with 2SB1375.

Audio frequency power amplifier applications.



PIN1 Base

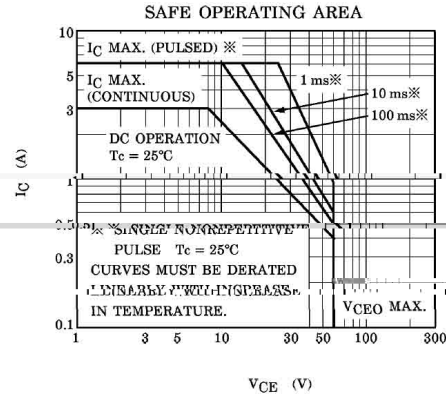
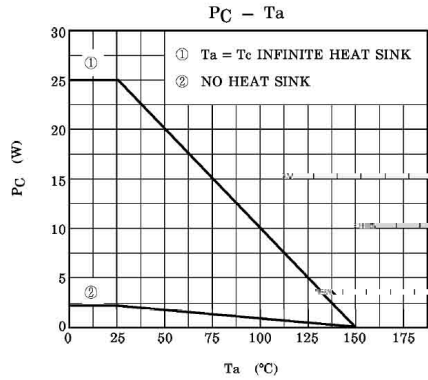
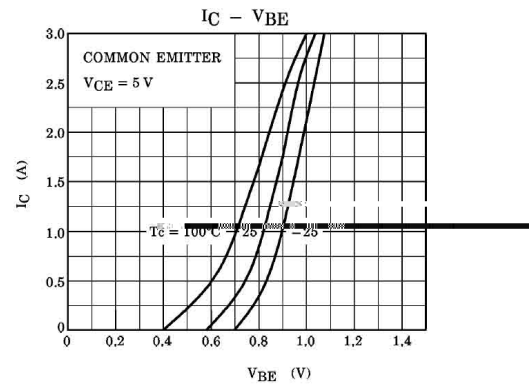
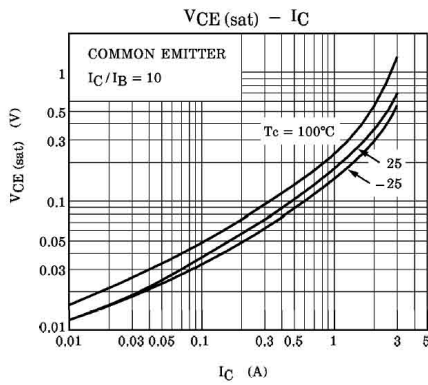
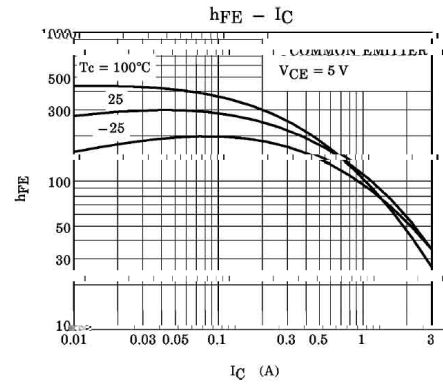
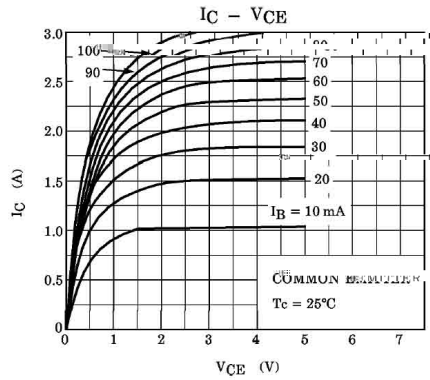
PIN 2 Collector

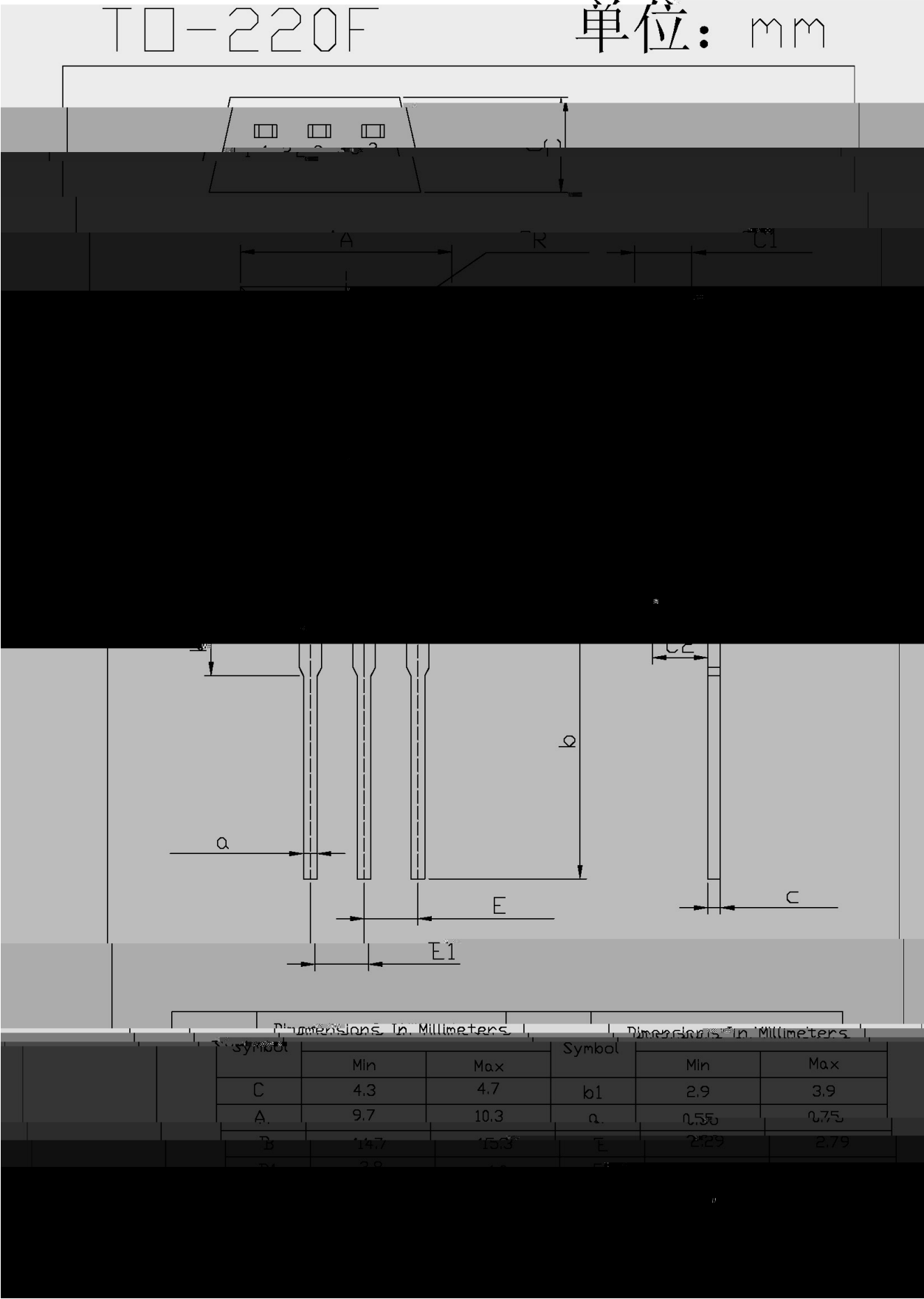
PIN 3 Emitter

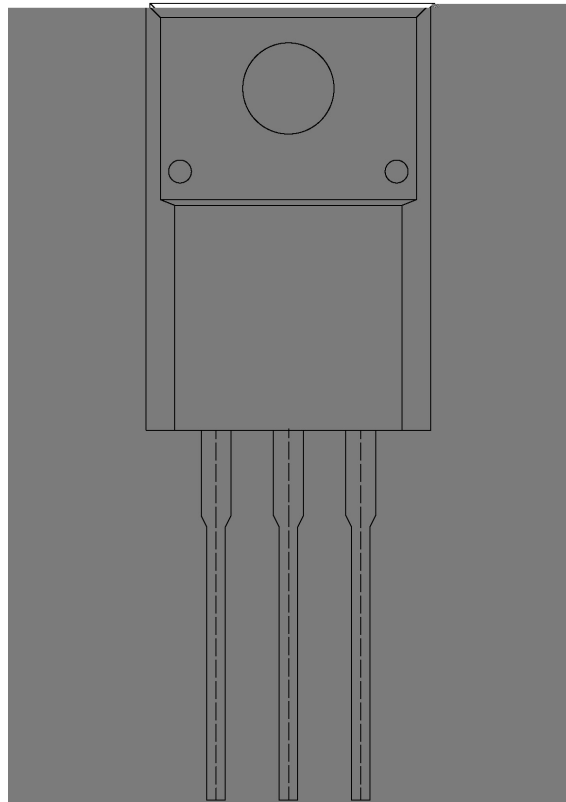
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	2	W
Collector Power Dissipation	$P_C (T_c=25^\circ\text{C})$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=50\text{mA}$ $I_B=0$	60			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60\text{V}$ $I_E=0$			100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=7.0\text{V}$ $I_C=0$			100	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5\text{V}$ $I_C=0.5\text{A}$	100		320	
	$h_{FE(2)}$	$V_{CE}=5\text{V}$ $I_C=2\text{A}$	20			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2\text{A}$ $I_B=0.2\text{A}$		0.4	1.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5\text{V}$ $I_C=0.5\text{A}$		0.75	1.0	V
Transition Frequency	f_T	$V_{CE}=5\text{V}$ $I_C=0.5\text{A}$		3.0		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$ $I_E=0$ $f=1\text{MHz}$		35		pF





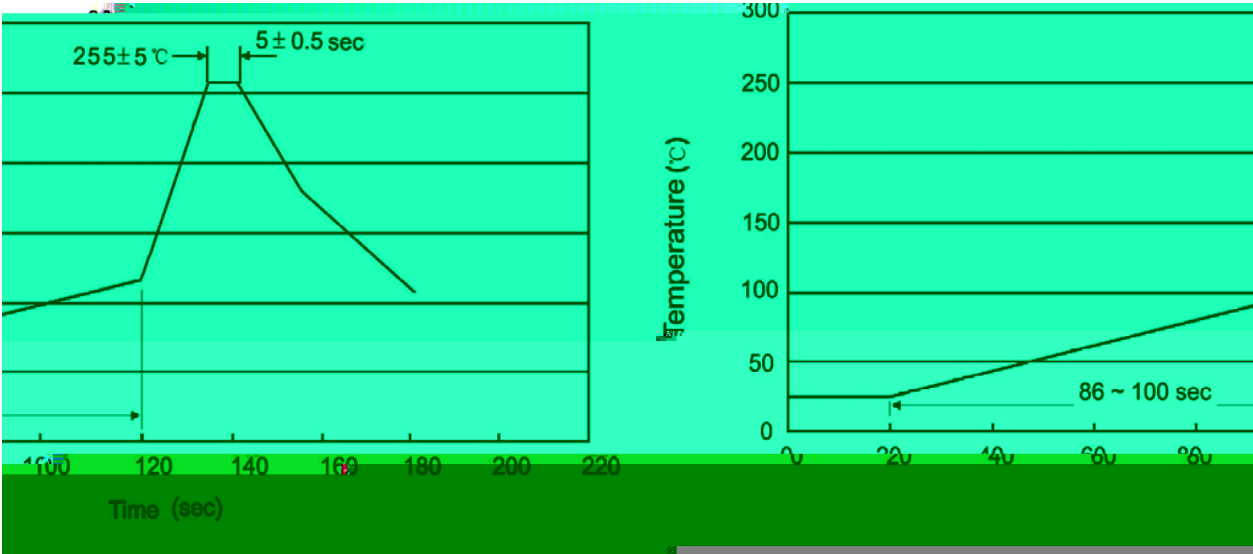


BR

D2012

Note:

BR: Company Code.



- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units		Dimension	(unit mm ³)
	Units/Bag	Bags/Inner Box	Units/Inner Box	
	/	/	/	